December 1994

National Semiconductor

LP265/LP365 Micropower Programmable **Quad Comparator**

General Description

The LP365 consists of four independent voltage comparators. The comparators can be programmed, four at the same time, for various supply currents, input currents, response times and output current drives. This is accomplished by connecting a single resistor between the $V_{\mbox{CC}}$ and I_{SET} pins.

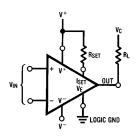
These comparators can be operated from split power supplies or from a single power supply over a wide range of voltages. The input can sense signals at ground level even with single supply operation. The unique output NPN transistor stages are uncommitted to either power supply. They can be connected directly to various logic system supplies so that they are highly flexible to interface with various logic families.

Application areas include battery power circuits, threshold detectors, zero crossing detectors, simple serial A/D converters, VCO, multivibrators, voltage converters, power sequencers, and high performance V/F converters, and RTD linearization.

Features

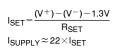
- Single programming resistor to tailor power consumption, input current, speed and output current drive capability
- Wide single supply voltage range or dual supplies (4 V_{DC} to 36 V_{DC} or $\pm 2.0 V_{DC}$ to $\pm 18 V_{DC}$)
- Low supply current drain (10 $\mu\text{A})$ and low power consumption (10 μ W/comparator) @ I_{SET} = 0.5 μ A $V_{CC} = 5_{VDC}$
- Uncommitted output stage—selectable output levels
- Output directly compatible with DTL, TTL, CMOS, MOS or other special logic families
- Input common-mode range includes ground
- Differential input voltage equal to the power supply voltage

Typical Connection

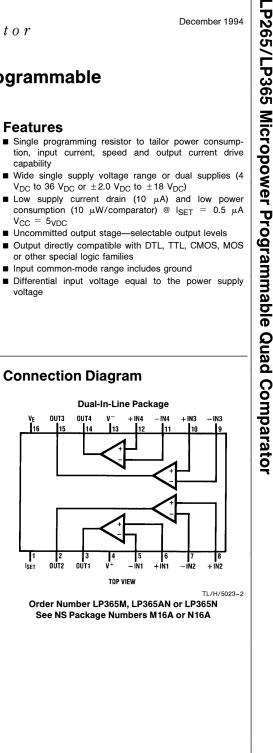


TL/H/5023-1

Programming Equation



Connection Diagram



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solute Maximum R litary/Aerospace specified se contact the National e/Distributors for availabilit	devices are required, Semiconductor Sales	Power Dissipation (Note 3) Τ _j Max θjA	M Package 500 mW 115°C 115°C/W	N Package 500 mW 115°C 90°C/W	
upply Voltage	36 V_DC or \pm 18 V_DC	Lead Temp.			
erential Input Voltage	\pm 36 V _{DC}	(Soldering—10 sec.)		260°C	
It Voltage (Note 1)	$-0.3V$ to $+36V_{DC}$	(Vapor Phase—60 sec.)	215°C		
0 ()	De	(Infrared—15 sec.)	220°C		
put Short Circuit to V _E (Note 2)	Continuous	Operating Temp. Range LP365:	$0^{\circ}C \leq$	$T_A \leq +70^{\circ}C$	
_{UT} with Respect to V _E V D Tolerance (Note 10)	E ^{−7V≤V} OUT [≤] VE ⁺ 36V 2000V	Storage Temp. Range	$-40^{\circ}C \le T$	A ≤ +150°C	

Electrical Characteristics (Note 4) Low power V_S=5V, I_{SET}=10 ~\mu A

			LP365A			LP365			
Symbol	Parameter	Conditions	Тур	Tested Limit (Note 5)	Design Limit (Note 6)	Тур	Tested Limit (Note 5)	Design Limit (Note 6)	Units (Limit)
V _{OS}	Input Offset Voltage	V _{CM} =OV, R _S =100	1	3	6	3	6	9	mV (Max)
I _{OS}	Input Offset	V _{CM} =0V	2	20	50	4	25	75	nA
	Current	LP265				4	25	150	(Max)
IB	Input Bias	V _{CM} =0V	10	50	125	15	75	200	nA
	Current	LP265				15	75	300	(Max)
A _{VOL}	Large Signal Voltage Gain	R _L =100k	500	50	50	300	25	25	V/mV (Min)
V _{CM} Input Common- Mode Voltage Range			0	ο		0	ο	V (Max)	
			3	3		3	3	V (Min)	
CMRR	Common-Mode Rejection Ratio	$0 \le V_{CM} \le 3V$	85	75	70	80	75	70	dB (Min)
PSRR	Supply Voltage Rejection Ratio	$\pm 2.5V \le V_S$ $\le \pm 3.5V$	75	65	65	70	65	65	dB (Min)
I _S	Supply Current	All Inputs = 0V, $R_L = \infty$	215	250	300	225	275	300	μA (Max)
V _{OH}	Output Voltage High	$V_{C}=5V,$ $V_{E}=0V,$ $R_{L}=100k$		4.9	4.5		4.9	4.5	V (Min)
V _{OL}	Output Voltage Low	V _E =0V		0.4	0.4		0.4	0.4	V (Max)
ISINK	Output Sink Current	V _E =0V, V _O =0.4V	2.4	1.2	0.6	2.0	0.8	0.4	mA (Min)
I _{LEAK}	Output Leakage Current	V _C =5V, V _E =0V	2	50	5000	2	100	5000	nA (Max)
t _R	Response Time	$V_{CC} = 5V,$ $V_{E} = 0V,$ $R_{L} = 5k,$ $C_{L} = 10 \text{ pF}$ (Note 7)	4			4			μs

Symbol		Conditions	LP365A			LP365			
	Parameter		Тур	Tested Limit (Note 5)	Design Limit (Note 6)	Тур	Tested Limit (Note 5)	Design Limit (Note 6)	Units (Limit)
V _{OS}	Input Offset Voltage	V _{CM} =0V, R _S =100	1	3	6	3	6	9	mV (Max)
I _{OS}	Input Offset Current	V _{CM} =0V LP265	5	50	100	10 10	90 90	200 500	nA (Max)
IB	Input Bias Current	V _{CM} =0V LP265	60	200	500	80 80	300 300	500 800	nA (Max)
A _{VOL}	Large Signal Voltage Gain	R _L =15k	500	100	100	500	100	100	V/mV (Min)
V _{CM} Ir	Input Common- Mode Voltage			-15	- 15		-15	- 15	V (Max)
	Range			13	13		13	13	V (Min)
CMRR	Common-Mode Rejection Ratio	−15V≤V _{CM} ≤13V	85	75	70	80	75	70	dB (Min)
PSRR	Supply Voltage Rejection Ratio	$\pm 10V \le V_S$ $\le \pm 15V$	80	70	70	75	70	70	dB (Min)
IS	Supply Current	All Inputs = 0V, $R_L = \infty$, LP265	2.6	3	3.3	2.8 2.8	3.5 3.5	3.7 4.3	mA (Max)
V _{OH}	Output Voltage High	$V_{C}=5V,$ $V_{E}=0V,$ $R_{L}=100k$		4.9	4.5		4.9	4.5	V (Min)
V _{OL}	Output Voltage Low	V _E =0V		0.4	0.4		0.4	0.4	V (Max)
ISINK	Output Sink Current	V _E =0V, V _O =0.4V	10	8	5.5	7.5	6	4	mA (Min)
I _{LEAK}	Output Leakage Current	$V_{C} = 15V,$ $V_{E} = -15V$	5	50	5000	5	50	5000	nA (Max)
t _R	Response Time	$V_{CC} = 5V,$ $V_{E} = 0V,$ $R_{L} = 5k,$ $C_{L} = 10 \text{ pF}$ (Note 7)	1.0			1.0			μs

Note 1: The input voltage is not allowed to go 0.3V above V⁺ or -0.3V below V⁻ as this will turn on a parasitic transistor causing large currents to flow through the device.

Note 2: Short circuits from the output to V⁺ may cause excessive heating and eventual destruction. The current in the output leads and the V_E lead should not be allowed to exceed 30 mA. The output should not be shorted to V⁻ if V_E \leq (V⁻) + 7V.

Note 3: For operating at elevated temperatures, these devices must be derated based on a thermal resistance of θ_{jA} and T_j max. $T_j = T_A + \theta_{jA}P_D$. Note 4: **Boldface numbers apply at temperature extremes.** All other numbers apply at $T_A = T_j = 25^{\circ}$ C. V + =5V, V - =0V, $I_{SET} = 10 \ \mu$ A, $R_L = 100$ k, and $V_C = 5V$ as shown in the Typical Connection diagram.

Note 5: Guaranteed and 100% production tested.

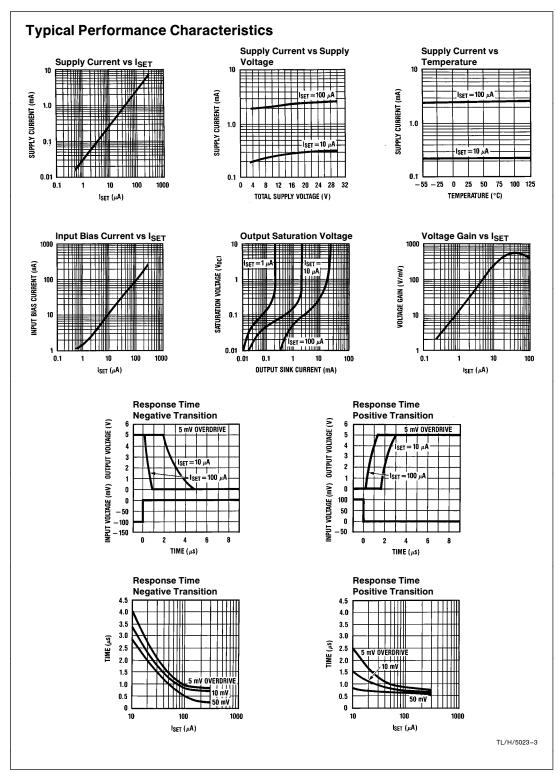
Note 6: Guaranteed (but not 100% production tested) over the operating temperature and supply voltage ranges. These limits are not used to calculate out-going quality levels.

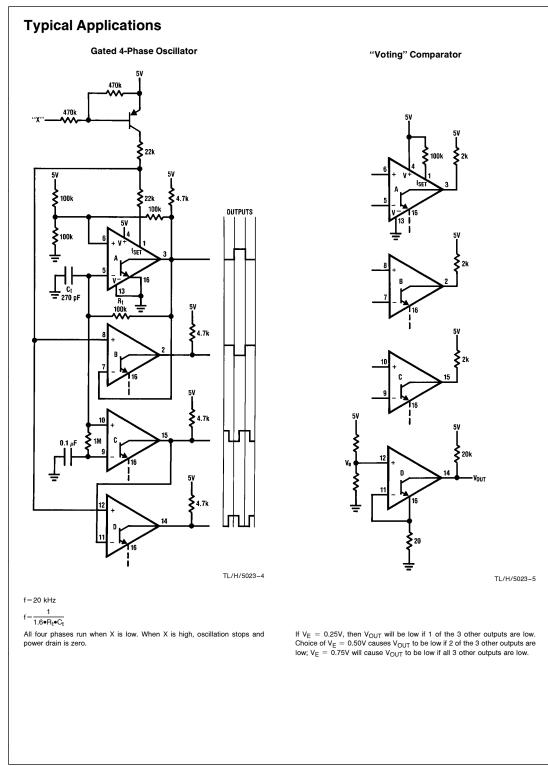
Note 7: The response time specified is for a 100 mV input step with 5 mV overdrive.

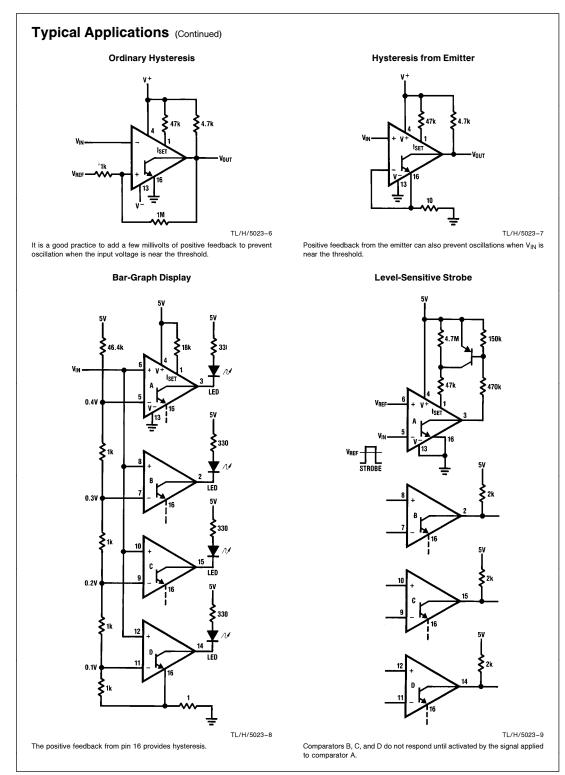
Note 8: Boldface numbers apply at temperature extremes. All other numbers apply at $T_A = T_j = 25^{\circ}$ C. $V^+ = +15$ V, $V^- = -15$ V, $I_{SET} = 100 \ \mu$ A, $R_L = 100$ k, and $V_C = 5$ V as shown in the Typical Connection diagram.

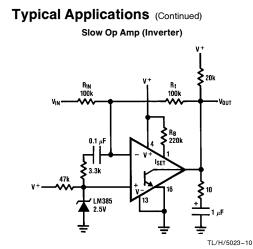
Note 9: See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

Note 10: Human body model, 1.5 k Ω in series with 100 pF.



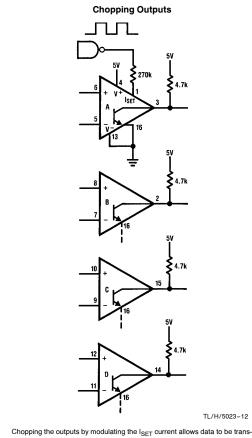






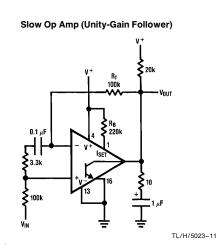
$R_B = V^+/20 \ \mu A$

Unlike most comparators, the LP365 can be used as an op amp, if suitable R-C damping networks are used.



TL/H/5023-12

mitted via opto-couplers, transformers, etc.



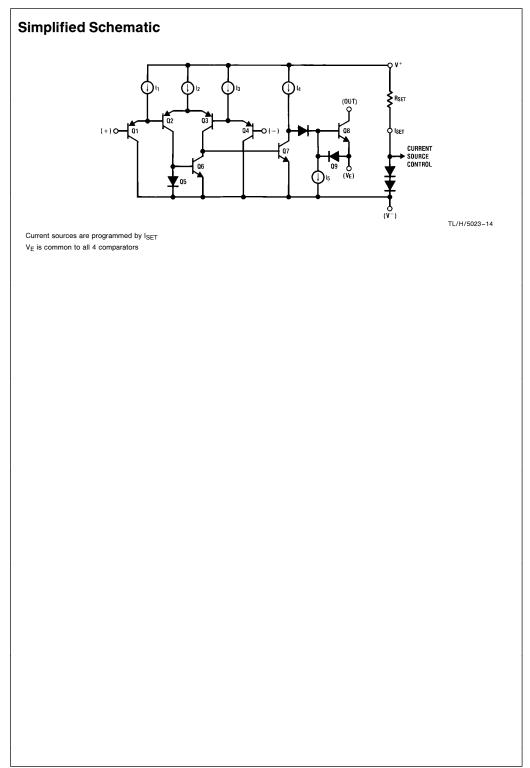
 $R_{B}=V^{+}/20~\mu A$

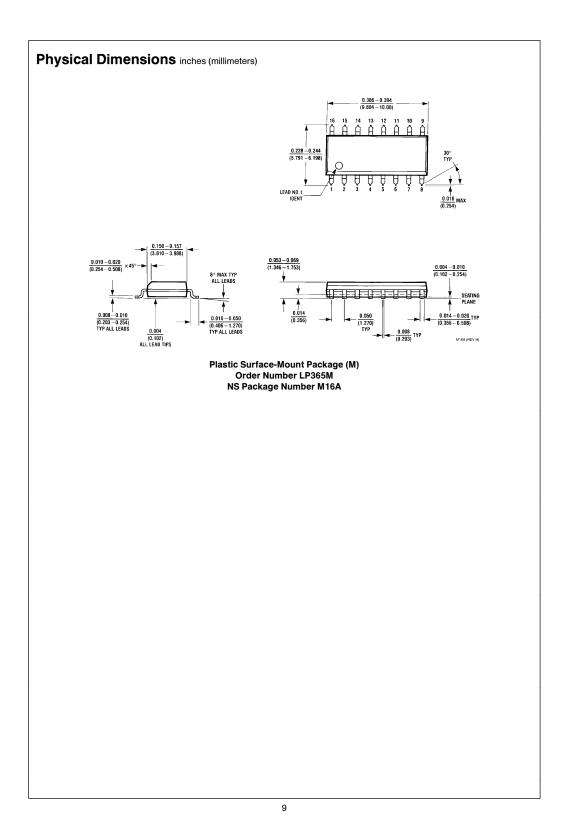
The LP365 can also be used as a high-input-impedance follower-amplifier with the damping components shown.

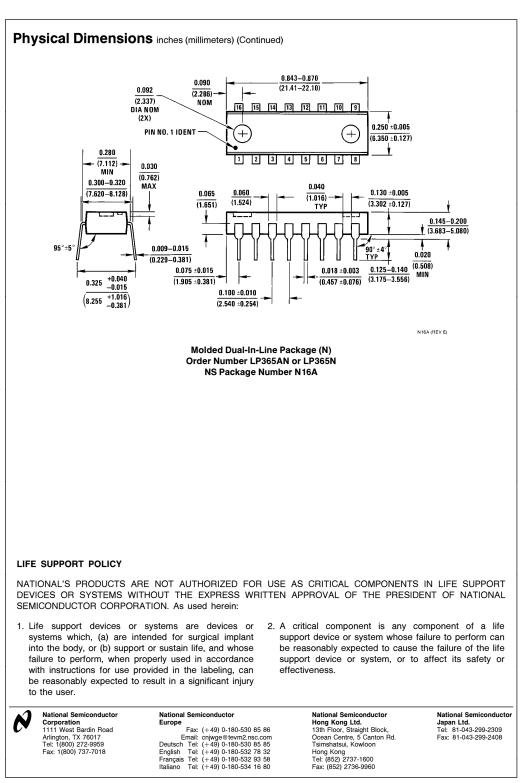
Low Battery Detector VRAT 470k 270k 5 10M 100k 0.1 uF LM385 1.2V 1 VRAT H Ş 10M .71 LOW Battery Alarm **≨**™ **₹**10M B PIEZO Ş RANSDUCER .5M ₽F TL/H/5023-13 $I_{S} @ 6V = 45 \ \mu A$ $I_S @ 3.8V = 1 \ \mu A$

f = 3 kHz

Comparator A detects when the supply voltage drops to 4V and enables comparator B to drive a piezoelectric alarm.







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